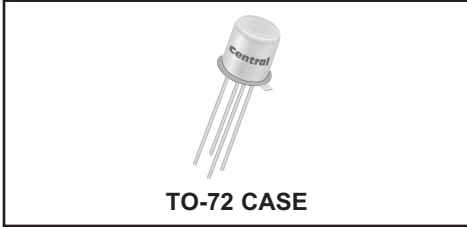


2N918

NPN SILICON RF TRANSISTOR



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N918 type is an NPN silicon RF transistor, manufactured by the epitaxial planar process and designed for high frequency amplifier and oscillator applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Continuous Collector Current	I_C	50	mA
Power Dissipation	P_D	200	mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	300	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	87.5	$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	58.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

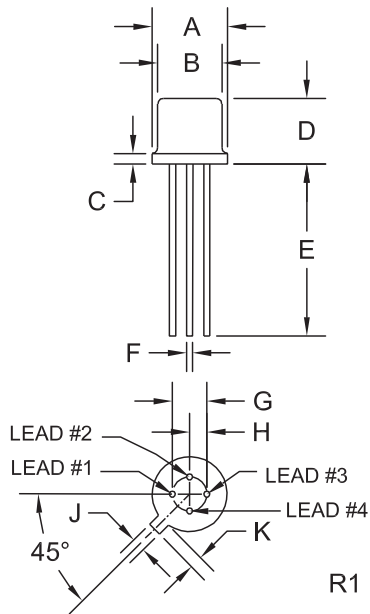
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=15\text{V}$		10	nA
I_{CBO}	$V_{CB}=15\text{V}, T_A=150^\circ\text{C}$		1.0	μA
BV_{CBO}	$I_C=1.0\mu\text{A}$	30		V
BV_{CEO}	$I_C=3.0\text{mA}$	15		V
BV_{EBO}	$I_E=10\mu\text{A}$	3.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.4	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.0	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=3.0\text{mA}$	20		
f_T	$V_{CE}=10\text{V}, I_C=4.0\text{mA}, f=100\text{MHz}$	600		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		1.7	pF
C_{ob}	$V_{EB}=0, I_E=0, f=1.0\text{MHz}$		3.0	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		2.0	pF
P_o	$V_{CB}=15\text{V}, I_C=8.0\text{mA}, f=500\text{MHz}$	30		mW
G_{pe}	$V_{CB}=12\text{V}, I_C=6.0\text{mA}, f=200\text{MHz}$	15		dB
η	$V_{CB}=15\text{V}, I_C=8.0\text{mA}, f=500\text{MHz}$	25		%
NF	$V_{CE}=6.0\text{V}, I_C=1.0\text{mA}, R_G=400\Omega, f=60\text{kHz}$		6.0	dB

R1 (11-September 2012)

2N918
NPN SILICON RF TRANSISTOR



TO-72 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.175	0.195	4.45	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
J	0.036	0.046	0.91	1.17
K	0.028	0.048	0.71	1.22

TO-72 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector
- 4) Case

MARKING:

FULL PART NUMBER

R1 (11-September 2012)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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